NANOFABRICATION RESEARCH INTHE RESEARCH CENTRE IN NANOSCIENCE AND NANOTECHNOLOGY (CIN2)

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Presentation to the NANOLITO Workshop 26th May 2009

OUTLINE

- Facilities
- Examples of research work
- Perspectives

ICN FACT SHEET

PEOPLE

Total 60

Including 13 nonresearchers

PUBLICATIONS 2007 (08)

Nr of publications:

59 (84)

Average Impact Factor: 3.76 (3.96)

PROJECTS

11 National	1.2 M€
12 European	5.2 M€
4 SME's	0.2 M€
Total	6.6 M€

INDUSTRIAL ACTIVITIES

1 Spin-off 5 Patents With NANÒNICA incorporating nanoparticles in wools (2007)

With ENDOR on synthesis and medical applications of advanced nanomaterials. (2007)

With **BIOINGENIUM** in a feasibility study to produce hormones for veterinary use. (2007)

With NANOINK on a NDA-covered agreement concerning patterning and ink applications (2007)

With LEITAT – ACONDICIONAMIENTO TARRASSENSE on textiles suitable for UV protection (2007)

Catalysis

-Surface-supported Au nanoparticles for catalytic applications

Self-assembly and Nanofabrication (joint with VTT)

-Capillary-directed sedimentation on topologically patterned substrates

Drug and chemical compounds delivery

-Compounds encapsulation in Metal-Organic nanospheres

Nanobiomedicine

-Cell identification with Au nanoparticles by means of H ion reduction

-Au nanoparticles functionalized with peptide molecules

CIN2 COMMON EQUIPMENT

• E-beam Metal Evaporators

- For non-magnetic materials
- For magnetic materials (e-beam and sputtering)
- SEM
 - Environmental, 150 mm wafer undergoing purchasing process
 - High resolution undergoing purchasing process
- TEM (200kV) undergoing purchasing process
- X-ray Diffraction
 - Powder XRD (for Co, Fe, Ni, ... NPs)
 - Thin films XRD (High resolution, SAXS, reflectometry,texture, etc.)
- XPS/UPS System
- SQUID
- Mid-far IR spectrometer
- AFM
- Nanoimprinter 50 mm wafer
- Focused ion beam (crossed-beam)

Also

wide range of specialist equipment in each research group

- Theory and Atoms on Surfaces
- > Nanoparticles, NPs in matrices and energy research

Nanofabrication and Nanometrology

- > Physical Properties of Nanostructures
- Nanobiosensors

THEORY AND NANOSTRUCTURES MANIPULATION

P Ordejon, P Gambardella and J Fraxedas

- Atomistic simulations
- Magnetic atoms/molecules on surfaces
- Metal-organic nanostructures
- Small molecules

NANOPARTICLES, NPS IN MATRICES AND ENERGY RESEARCH

V Puntes, D Ruiz-Molina, P Gomez-Romero, M Lira-Cantu

- Inorganic nanoparticles
- Core-shell NPs
- Molecular electronics
- Metal-organic materials
- Energy storage and conversion
- Solar cells

NANOFABRICATION AND NANOMETROLOGY

C M Sotomayor Torres, D Ruiz-Molina, S Valenzuela and A Bachtold

• Self-assembly

- Focused ion and electron beam lithography
- Dip pen Lithography
- Nanoimprint lithography
- Nanometrology

Other teams using nanfabrication facilities are those of L Lechuga (plasmonics for biosensors) and J Fraxedas (synchrotorn-based approaches) ¹⁰

Self-assembly of 3D colloidal crystals





W Khunsin, G Kocher et al, to be published



Quality improvement using acoustic noise

Concept of "opposite beads"

p(r) - probability of finding an opposite beads within a radius r, for a given tolerance parameter $\boldsymbol{\epsilon}$ for the exact location of the spheres



At sphere 'A'

$$p(r) = \frac{\sum_{A \neq B, C} \chi_r(\overrightarrow{AB}) \chi_{\varepsilon}(\overrightarrow{AB} + \overrightarrow{AC})}{\sum_{A \neq B} \chi_r(\overrightarrow{AB})}$$

$$\chi_{y}(\vec{R}) = \begin{cases} 1 & if \quad \left| \vec{R} \right| < y \\ 0 & else \end{cases}$$

Global sum: weighted average



Stochastic-resonance in photonic crystal growth

<u>D = 368 nm</u>

r = 5.5 μ m \approx 15D, and ϵ = 43 nm \approx 0.12D



Particles self-assembled on patterned Silicon and SOI



Etched silicon substrate

PMMA opal self-assembled in basins in etched silicon substrate

Joint patent 2007, S Arpianen, J Ahopelto, F Jonsson and C M Sotomayor Torres.

The PHAT project 14



Molecular self-assembly assisted by nanoimprinting



Surface functionalisation









D Ruiz group

DPL Different writing modes

Static Writing

Dynamic Writing



Reverse Nanoimprint Lithography



N Kehagias et al J Vac Sci Technol B 24, 3002 (2006)



Reverse UV Nanoimprinting technique

- No residual layer
- No need for anti-adhesive treatment of the stamp
- The same photocurable polymer is used
- High resolution (stamp dependent)
- High throughput (<2 min)



Patterned area 5 x 5 mm2





N. Kehagias *et. al*, *J. Vac. Sci. Technol. B* **24**, 3002, (2006) N. Kehagias *et. al*, Nanotechnology, 18, 175303, (2007)

Polymer double layer grating by RUV NIL



a/ SEM image of a large (>50 μ m) double layer grating. b/ Fourier transform of a/ showing good homogeneity of lines over the whole surface with limited dispersion in size and position c/ Far -field optical image of diffracted light by the 3D grating.

N Kehagias_et al., J. Vac. Sci. Technol. B 24, 3002, 2006

Modelling of the NIL process

Assume resist is an incompressible viscous fluid \rightarrow non-stationary Navier-Stokes equations in velocity-pressure

$$\operatorname{Re}\left[\frac{\partial \mathbf{V}}{\partial t} + (\mathbf{V} \cdot \nabla)\mathbf{V}\right] = -\nabla P + \Delta \mathbf{V}, \qquad \frac{\nabla \cdot \mathbf{V} = 0,}{\mathbf{V} = (v^{x}, v^{y}, v^{z}),}$$

Re is the Reynolds number, V is the stamp velocity, P is the pressure. Also includes characteristic lateral size of the stamp and the density and the dynamic viscosity of the resist.



Stamp bending due to non-homogeneous stamp design.

Areas with high resist pressure result in a higher residual layer thickness.

Modelling of the NIL process

Optical microscope image.

Profilometer measurement, Showing stamp bending during the NIL process

Simulated "RGB" images of residual layer height distribution. White iso-lines indicate the stamp bending in nm (190nm-150 nm= 40nm of stamp bending)



Modelling of the NIL process



Simulated scan along the black line



Subwavelength diffraction



Sub-wavelength features within periodic test structure Line-width, height, defects affect the relative efficiency of orders in far-field diffraction.

24

 Models (FDTD and Rigorous Coupled Wave Analysis) show sensitivity to dimension changes of <10nm



 Shows presence of defect – missing 50nm lines



T. Kehoe et al, Sub-wavelength optical diffraction and photoacoustic metrologies for the characterisation of nanoimprinted structures, Proc. SPIE 6922 (2008) 69210F

Metrology with Photoacoustic spectroscopy



Collaboration with Juerg Bryner & Prof Dr Juerg Dual, Centre of Mechanics, ETH 22 urich

Photoacoustic Metrology of Nanoimprint Polymers

- Good acoustic impedance difference
- Damping in polymer not excessive
- Strong signal from both interfaces
 Top interface: Al/polymer
 Bottom interface: polymer/Si

Physical parameters calculated from speed and thickness – Young's modulus (E) and Poisson's ratio (n)

$$c_{p} = \sqrt{\frac{E(1-v)}{\rho(1+v)(1-2v)}}$$



T. Kehoe et al, Proc. Acoustics08 Paris 2517, 2008

PHYSICAL PROPERTIES OF NANOSTRUCTURES

J Nogues, A Bachtold, S Valenzuela, J Santiso, C M Sotomayor Torres

Carbon nanotubes & Graphene

Spin transport

Nanoionics

Nanoscale thermal conduction

Nanophotonics

Phonons in Nanostructures

Carbon nanotubes and graphene



Electro-Mechanics



nanotube motor



graphene



single-electron spectroscopy

Bachtold et al

mechanical properties of graphene



Garcia-Sanchez, van der Zande, San Paulo, Lassagne, McEuen, Bachtold Nano Letters 8, 1399 (2008)

Transport properties of graphene



9 Tesla, 4 K

mobility $\sim 15\,^{\prime}000$ to $25\,^{\prime}000~cm^2/Vs$

Moser, Barreiro, Bachtold, APL 2007

Si membrane

Observations of confined acoustic phonons in silicon membranes

C. M. Sotomayor Torres^{*,1,2}, A. Zwick², F. Poinsotte², J. Groenen², M. Prunilla³, J. Ahopelto³, A. Mlayah², and V. Paillard²

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PHYSICAL REVIEW B 77, 045420 (2008)

Inelastic light scattering by longitudinal acoustic phonons in thin silicon layers: From membranes to silicon-on-insulator structures

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> M. Prunnila and J. Ahopelto VTT Micro and Nanoelectronics, P.O. Box 1000, FI-02044 VTT, Espoo, Finland (Received 18 July 2007; published 23 January 2008)

30 nm SOI + 400 nm BOX





3ω method and samples for nanoscale thermal measurements

- **Principle:** Temperature of the device lower if the substrate is more thermally conductive
- Method: Link the device temperature to the substrate thermal conductivity





Probes in contact with the pads of the chip fabricated at VTT

Schematics of a grease with nanoparticles and its nonplanar surface



P-Oliveir Chapuis

2D Defect Layer in 3D photonic crystals

Diffraction Measurements

Patterns from triangular 2D defect layers inscribed on top of 3D PMMA opals with different periodicity

For these lattice constant and laser wavelength, unpatterned parts show no pattern



G Kocher, C M Sotomayor Torres et al to be published

Buried 2D Defect Layer in a 3D photonic crystal





Diffraction patterns from buried 2D defect layer inscribed in PMMA opals

How to increase the light extraction of a polymer film?



 $1/4n^2 \approx 9.8\%$ of light extracted (n=1.6) ~ 90.2 % trapped in the material



Modification of emission pattern: micro-cavity



2.

Diffraction of trapped light: Photonic Crystals

Potential application: OLEDs

Nanoimprinted polymer photonic components



Emission of (CdSe)ZnS nanocrystals unaffected ny NIL
 Homogeneous distribution of nanocrystal in matrix essential
 Improvement of light emission by factor of 2.4

Plasmon-exciton coupling in printed photonic crystals



PL spectra of the dye doped polymer film with (red) and without (black) Au nanorods, PL spectra of dye doped polymer film with Au nanorods 2D imprinted with photonic crystal

V. Reboud, et al., Optics Express, 15, 12, 7190, 2007.

Summary and Perspectives in Nanofabrication

- A sound starting base for nanofabrication work to underpin research in CIN2.
- An enormous know-how pool on nanofabrication available. Logistics is a problem. "Viscous medium" is the other. Eg: 24 x 7.
- Procedures for efficient and timely work are needed to use access potential of CNM-ICTS Nanolithography clean room.
- Central pooling of information? Access via web?
- So far incomplete processing line for non-CMOS compatible fabrication. Access to CNM-ICTS Nanolithography covers part of processing needs. Many processes must be developed anew.
- Much work is carried out in collaboration with external partners through joint projects.
- Future looks much better with the new CIN2 building closer to completion.